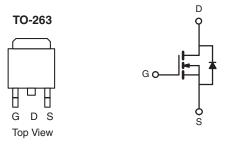


Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	30					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0015					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0020					
I _D (A)	120					
Configuration	Single					



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualifiedd
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N03-1m5L-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V_{DS}	30	V		
Gate-Source Voltage		V_{GS}	± 20	V		
Continuous Drain Currenta	T _C = 25 °C		120			
Continuous Drain Current	T _C = 125 °C	l _D	120			
Continuous Source Current (Diode Conduction) ^a	Is	120	Α			
Pulsed Drain Current ^b	I _{DM}	480				
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	82			
Single Pulse Avalanche Energy		E _{AS}	336	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	Б	375	W		
Maximum Fower Dissipation	T _C = 125 °C	P_D	125	VV		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)	co-Case (Drain)		0.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

SQM120N03-1m5L

Vishay Siliconix



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static				I.				
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	250	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0014	0.0015	Ω	
Duta On an On Olate Besteles and		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0023		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0028		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0016	0.0020		
Forward Transconductanceb	9fs	V _{DS} = 15 V, I _D = 30 A		-	190	-	S	
Dynamic ^b					•		,	
Input Capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = 15 V, f = 1 MHz		12 484	15 605	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$			2204	2755		
Reverse Transfer Capacitance	C _{rss}			-	860	1075	1	
Total Gate Charge ^c	Qg			-	179	270	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 10 \text{ V}, I_{D} = 120 \text{ A}$	-	34	-		
Gate-Drain Charge ^c	Q _{gd}			-	21	-		
Gate Resistance	R _g	f = 1 MHz		0.59	1.19	1.79	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	18	27		
Rise Time ^c	t _r	$V_{DD} = 15 \text{ V, } R_L = 0.3 \Omega$ $I_D \cong 50 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	11	17	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	64	96		
Fall Time ^c	t _f			-	11	17		
Source-Drain Diode Ratings and Chara	acteristics ^b						•	
Pulsed Current ^a	I _{SM}			-	-	480	Α	
Forward Voltage	V _{SD}	I _F = 60 A, V _{GS} = 0 V		-	0.81	1.5	٧	

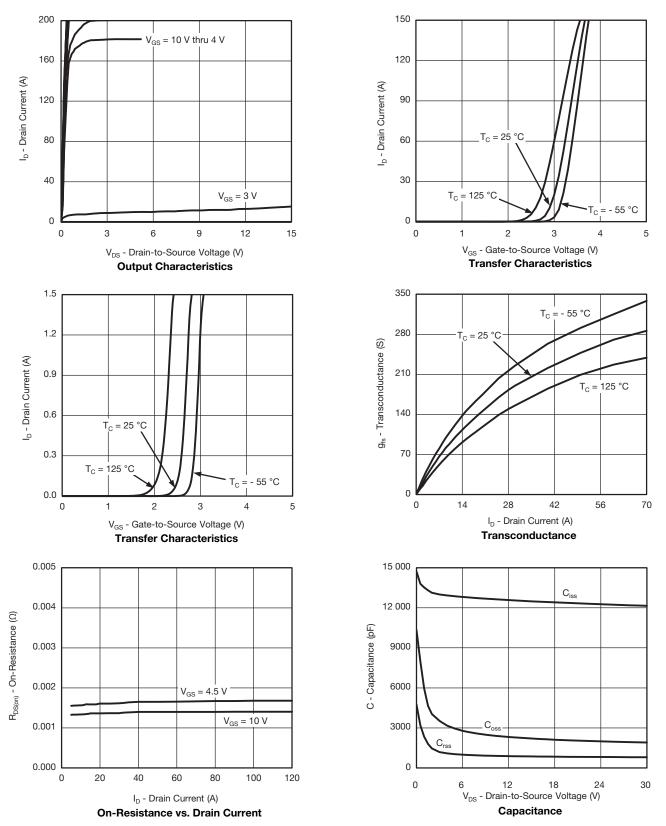
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



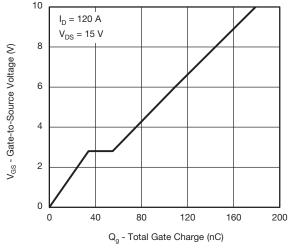
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



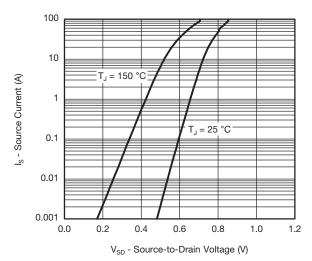
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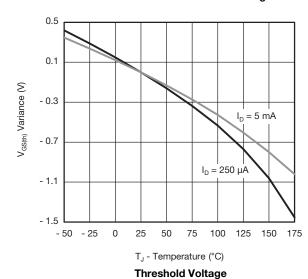
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}C$, unless otherwise noted)



Gate Charge

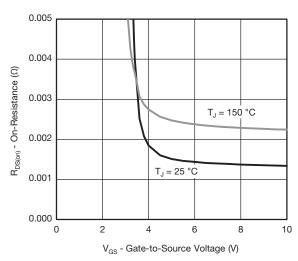


Source Drain Diode Forward Voltage

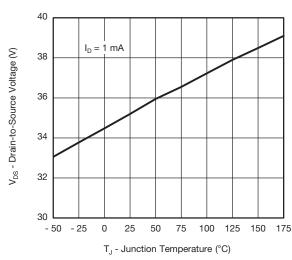


2.0 $V_{GS} = 10 \text{ V}$ $I_D = 30 \text{ Å}$ 1.7 R_{DS(on)} - On-Resistance (Normalized) 1.4 1.1 0.8 0.5 - 50 - 25 0 25 50 75 100 125 150 175 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



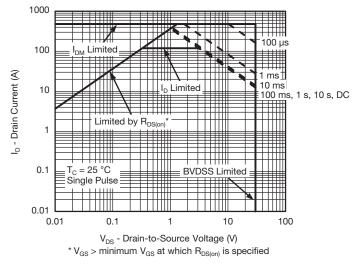
On-Resistance vs. Gate-to-Source Voltage



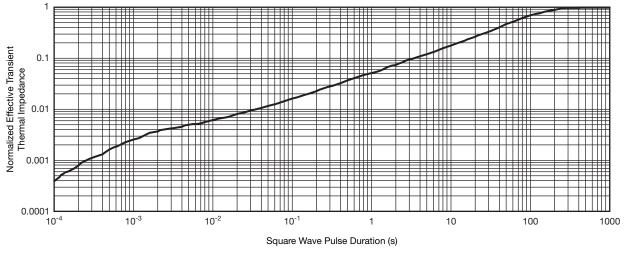
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

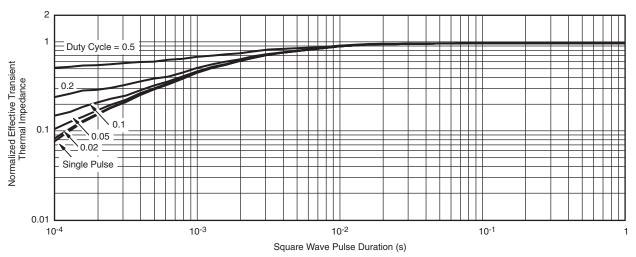


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67333.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

	INCHES		HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4 0.010 BSC		BSC	0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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